



6N65-P

Power MOSFET

6.2A, 650V N-CHANNEL POWER MOSFET

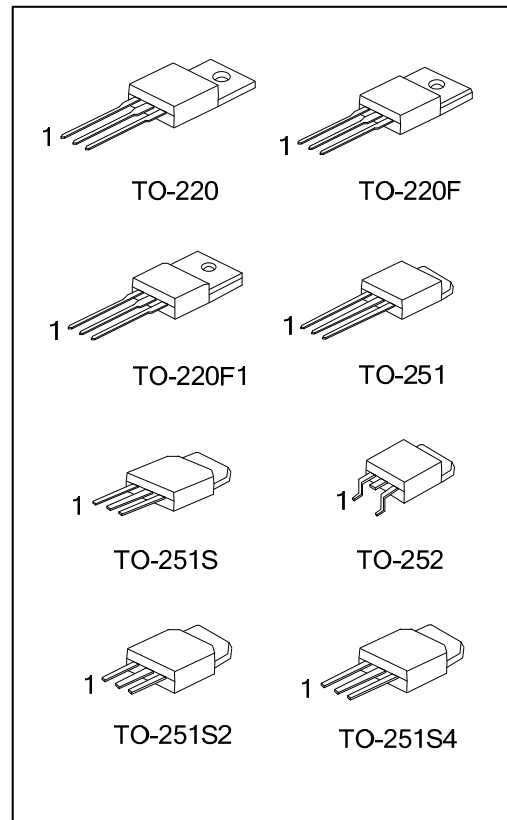
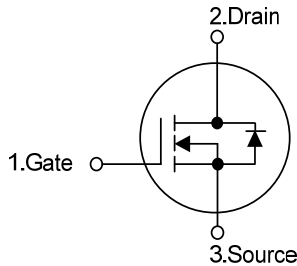
■ DESCRIPTION

The UTC **6N65-P** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

- * $R_{DS(ON)} < 2.0\Omega$ @ $V_{GS} = 10V, I_D = 3.1A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



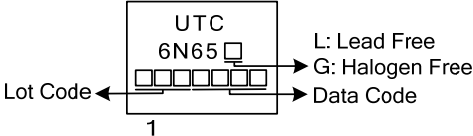
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N65L-TA3-T	6N65G-TA3-T	TO-220	G	D	S	Tube
6N65L-TF1-T	6N65G-TF1-T	TO-220F1	G	D	S	Tube
6N65L-TF3-T	6N65G-TF3-T	TO-220F	G	D	S	Tube
6N65L-TM3-T	6N65G-TM3-T	TO-251	G	D	S	Tube
6N65L-TMS-T	6N65G-TMS-T	TO-251S	G	D	S	Tube
6N65L-TMS2-T	6N65G-TMS2-T	TO-251S2	G	D	S	Tube
6N65L-TMS4-T	6N65G-TMS4-T	TO-251S4	G	D	S	Tube
6N65L-TN3-R	6N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>6N65L-TA3-T</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TM3: TO-251, TN3: TO-252, TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	6.2	A
Continuous Drain Current		I_D	6.2	A
Pulsed Drain Current (Note 2)		I_{DM}	24.8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	130	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F/TO-220F1		40	W
	TO-251/TO-251S		55	W
	TO-251S2/TO-251S4 TO-252			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 7.2\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252		110	$^\circ\text{C}/\text{W}$
	TO-220		1.0	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	3.2	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252		2.27	$^\circ\text{C}/\text{W}$

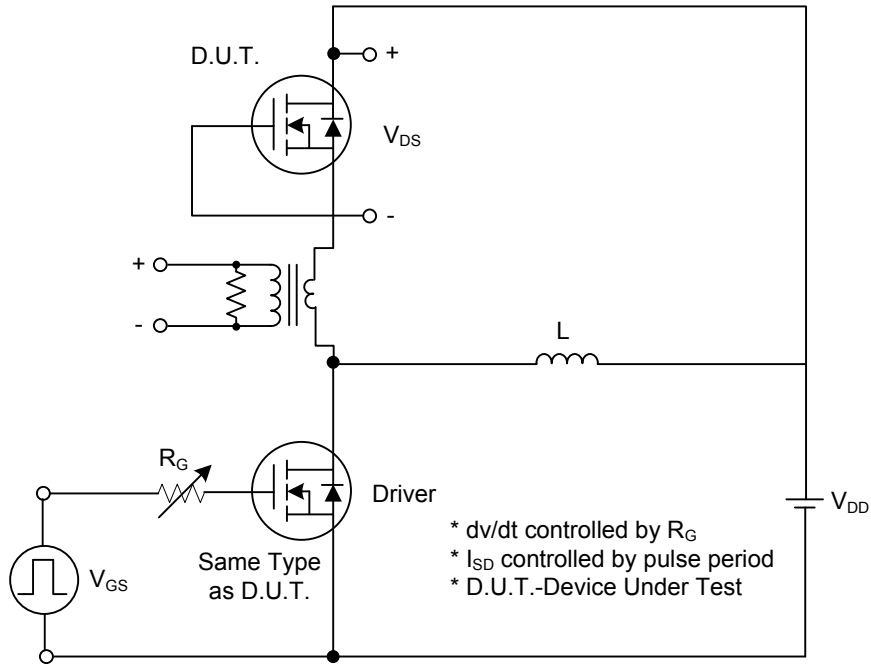
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.53		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 3.1A		1.6	2	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		800	1000	pF
Output Capacitance	C _{OSS}			80	120	pF
Reverse Transfer Capacitance	C _{RSS}			10	25	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =30V, I _D =0.5A, R _G =25Ω (Note 1, 2)		40	60	ns
Turn-On Rise Time	t _R			40	60	ns
Turn-Off Delay Time	t _{D(OFF)}			140	160	ns
Turn-Off Fall Time	t _F			60	80	ns
Total Gate Charge	Q _G	V _{DS} =50V, I _D =1.3A, V _{GS} =10V (Note 1, 2)		26	90	nC
Gate-Source Charge	Q _{GS}			5.6		nC
Gate-Drain Charge	Q _{GD}			6.0		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 6.2 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				6.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				24.8	A

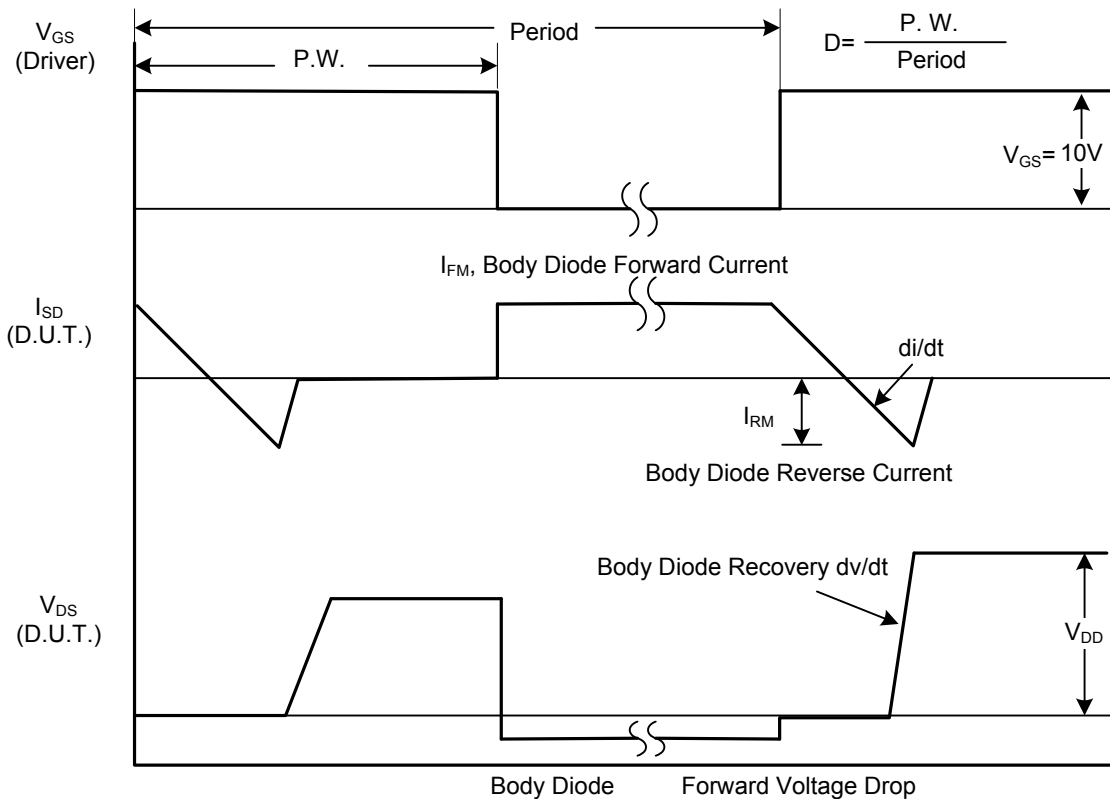
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

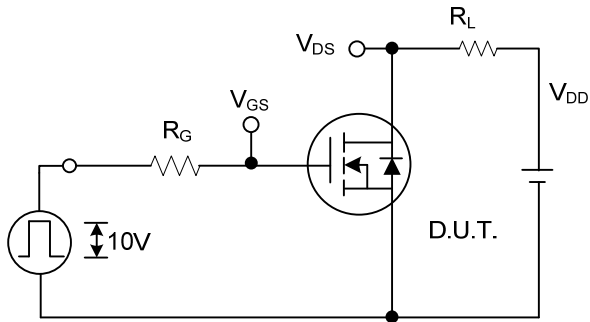


Peak Diode Recovery dv/dt Test Circuit

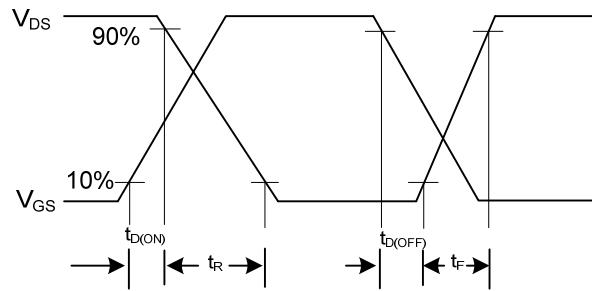


Peak Diode Recovery dv/dt Waveforms

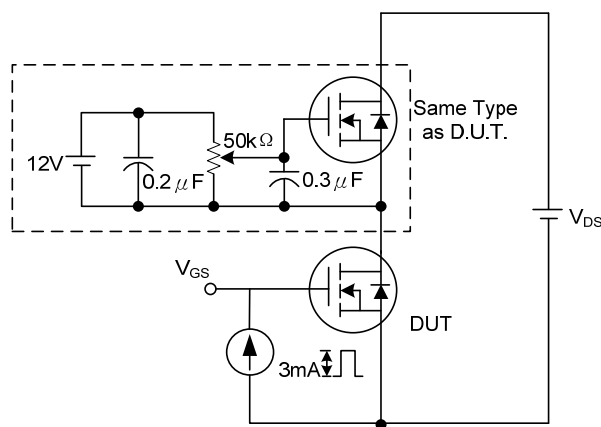
TEST CIRCUITS AND WAVEFORMS (Cont.)



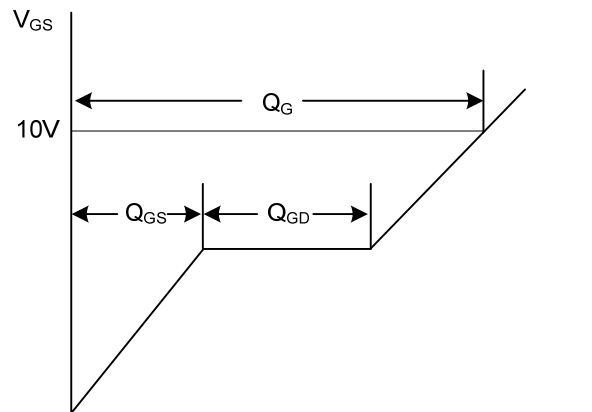
Switching Test Circuit



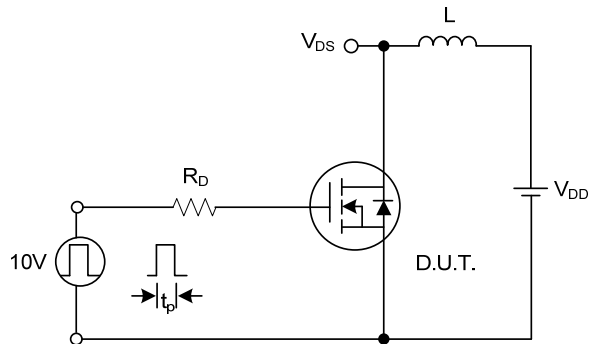
Switching Waveforms



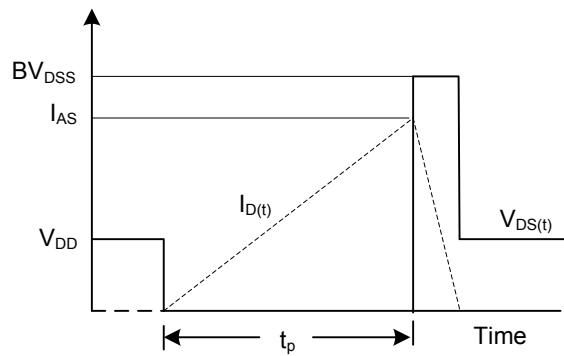
Gate Charge Test Circuit



Gate Charge Waveform

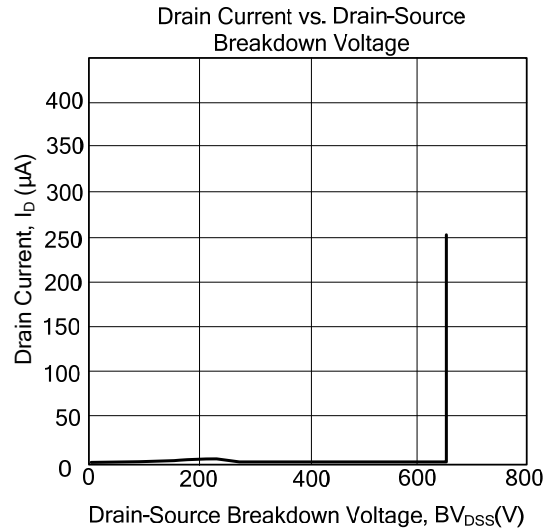
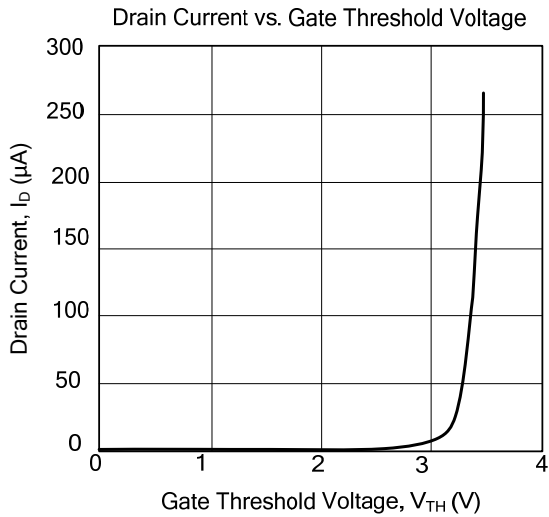
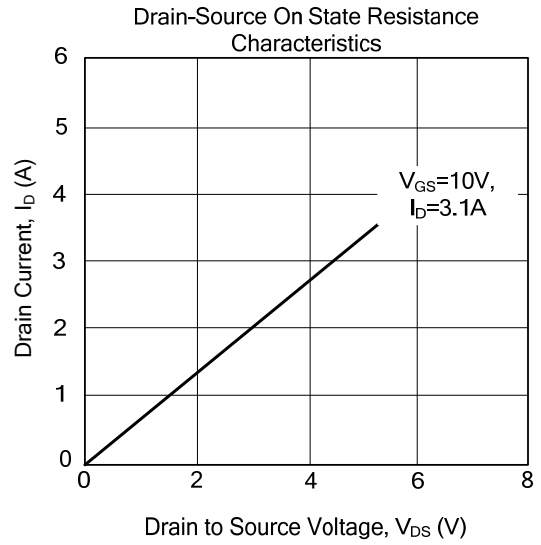
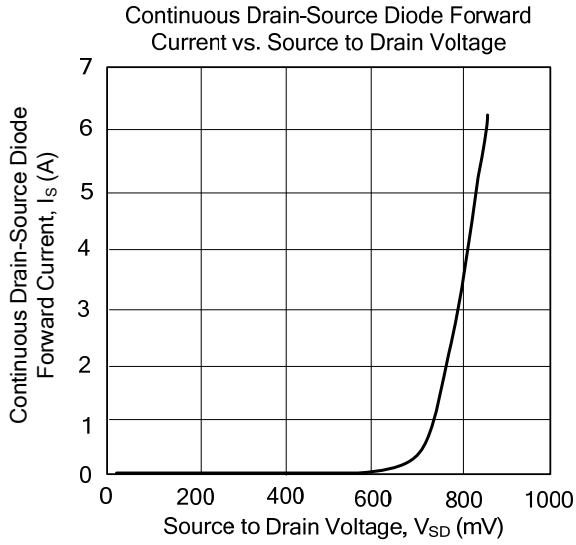


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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